

PATENT ASSIGNMENT

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
The Fox Group, Inc.	01/09/2013
RECEIVING PARTY DATA	
Name:	Kyma Technologies, Inc.
Street Address:	8829 Midway West Road
City:	Raleigh
State/Country:	NORTH CAROLINA
Postal Code:	27617
PROPERTY NUMBERS Total: 10	
Property Type	Number
Patent Number:	6218269
Patent Number:	6472300
Patent Number:	6476420
Patent Number:	6479839
Patent Number:	6555452
Patent Number:	6559038
Patent Number:	6559467
Patent Number:	6599133
Patent Number:	6849862
Patent Number:	6890809
CORRESPONDENCE DATA	
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ATTORNEY DOCKET NUMBER:	0000352120
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NAME OF SUBMITTER:	Matthew T. Currie/N.Deane
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PATENT ASSIGNMENT

This PATENT ASSIGNMENT is by The Fox Group, Inc., a California corporation, with its principal offices at 54 Jennie Dade Lane, Sperryville, VA 22740 (the "*Assignor*"), with regard to the following.

WHEREAS, Assignor has been granted or assigned the patents referenced on Exhibit A attached hereto (the "*Patents*"); and

WHEREAS, Assignor and Kyma Technologies, Inc., a Delaware corporation ("*Assignee*"), have entered into an Exclusive License and Sublicense Agreement dated as of September 28, 2010 (the "*License Agreement*") under the terms of which Assignee has exercised an option to acquire the entire right, title and interest in and to said Patents.

IN WITNESS THEREOF, in consideration of One Dollar (\$1.00) and for other good and sufficient consideration the receipt of which is hereby acknowledged, the Assignor has sold, assigned, transferred, and set over, and by these presents does sell, assign, transfer and set over, unto Assignee, its successors, legal representatives and assigns, the entire right, title and interest in and to the Patents, and reissues and extensions of said Patents, and all rights under the Paris Convention for the Protection of Industrial Property, together with all claims by Assignor for damages by reason of past infringement of the Patents with the right to sue for, and collect the same for Assignee's own use and benefit, and for the use and benefit of its successors, assigns and other legal representatives; the same to be held by Assignee, for its own use and behalf and the use and behalf of its successors, legal representatives, and assigns, to the full end of the term or terms for which said Patents have been granted as fully and entirely as the same would have been held by Assignor had this sale and assignment not been made;

AND for the same consideration, the Assignor hereby covenants and agrees to and with the Assignee, its successors, legal representatives and assigns, that, at the time of execution and delivery of these presents, the Assignor is the sole and lawful owner of the entire right, title and interest in and to the Patents and the invention set forth therein and that the same are unencumbered, and that the Assignor has good and full right and lawful authority to sell and convey the same in the manner herein set forth;

AND for the same consideration, the Assignor hereby covenants and agrees to and with the Assignee, its successors, legal representatives and assigns that the Assignor will, if counsel of the Assignee, or the counsel of its successors, legal representatives and assigns, shall advise that any proceeding in connection with said Patents or the invention set forth therein, or any proceeding in connection with said Patents and the invention set forth therein in any foreign country, including interference proceedings, is lawful and desirable, or any reissue or extension of said Patents to be obtained thereon, is lawful and desirable, sign all papers and documents, take all lawful oaths, and do all acts necessary or required to be done for the procurement, maintenance, enforcement and defense of said Patents for said invention, without charge to the Assignee, its successors, legal representatives and assigns, but at the cost and expense of Assignee, its successors, legal representatives and assigns;

AND the Assignor hereby requests that the Commissioner of Patents transfer registered ownership of said Patents, and any reissuance or extension thereof, to the Assignee for the sole use and benefit of the Assignee, its successors, legal representatives and assigns.

Dated: 9 JANUARY, 2013

THE FOX GROUP, INC.

By: Bernard P. O'Meara
Name: Bernard P. O'Meara
Title: President

EXHIBIT A

PATENTS

Patent Number	Status	Description	Applied	Granted	Country
6,218,269	G/TDII	Process for producing III-V nitride P-N junctions and P-I-N junctions and resulting structures	11/18/1998	4/17/01	USA
6,472,300	G/TDII	Method for growing P-N homojunction-based structures utilizing HVPE techniques	5/18/2001	10/29/02	USA
6,476,420	G/TDII	P-N Homojunction-based structures utilizing HVPE grown III-V compound layers	5/17/2001	11/5/02	USA
6,479,839	G/TDII	III-V compound semiconductor device with an $\text{Al}_x\text{ByIn}_z\text{Ga}_{1-x-y-z}\text{N}$ non-continuous quantum dot layer	5/18/2001	11/12/02	USA
6,555,452	G/TDII	Method for growing P-type III-V compound material utilizing HVPE techniques	8/14/2000	4/29/03	USA
6,559,038	G/TDII	Method for growing P-N heterojunction-based structures utilizing HVPE techniques	8/14/2000	5/6/03	USA
6,559,467	G/TDII	P-N heterojunction-based structures utilizing HVPE grown III-V compound layers	5/17/2001	5/6/03	USA
6,599,133	G/TDII	Method for growing III-V compound semiconductor structures with an integral non-continuous quantum dot layer utilizing HVPE techniques	5/18/2001	7/29/03	USA
6,849,862	G/TDII	III-V compound semiconductor device with an $\text{Al}_x\text{ByIn}_z\text{Ga}_{1-x-y-z}\text{N}_{1-a-b}\text{PaAs}_b$ non-continuous quantum dot layer	5/18/2001	2/1/05	USA
6,890,809	G/TDII	Method for fabricating a P-N heterojunction device utilizing HVPE grown III-V compound layers and resultant device	8/9/2002	5/10/05	USA

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